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ECE Dept.

Exam.

Internal Assessment

Even Sem(2018-19)

SECOND INTERNAL ASSESSMENT

Sem: VIII

Date: 11/04/2019

Sub: Fiber Optics and N/W

Time: 3.00-4.00 pm

Sub. Code: 15EC82

Max. Marks: 25

Note: Answer two full questions, draw sketches wherever necessary.

Q. No	Description of Question	Marks	CO	RBT LEVEL
1	a Explain with suitable energy band diagram, the working of a heterostructure LED.	6	C402.3	L1,L2
	b A heterostructure LED has $T_r = 30$ nsec, $T_{nr} = 100$ nsec with a drive current of 40mA and $\lambda = 1310$ nm. Calculate a. Bulk recombination life time b. Internal Quantum Efficiency c. Internal Power level.	6	C402.3	L1,L2
OR				
2	a Explain with a suitable energy band diagram, the 3 major processes involved in the operation of a Laser diode.	6	C402.3	L1,L2
	b Explain with a suitable diagram the working of Fabry-Perot resonator Laser diode and compare it with DFB laser.	6	C402.3	L1,L2
3	a What are the requirements of a photo detectors? Explain the working of a PIN photo diode with a suitable diagram.	7	C402.3	L1,L2
	b A laser source has a cavity length of $500\mu\text{m}$, $R_1 = R_2 = 0.32$ and $\alpha = 10\text{cm}^{-1}$. Calculate the threshold gain of laser cavity and show it using characteristics of laser diode.	6	C402.3	L1,L2
OR				
4	a Discuss the various types of noises associated with optical detector and obtain the expression for SNR.	7	C402.3	L1,L2
	b A Silicon photo diode has quantum efficiency of 65% at a wavelength of 900nm. A power of $0.5\mu\text{W}$ produces a multiplied current of $10\mu\text{A}$. Calculate I_p (Primary Photocurrent) and M (multiplication factor) of photodiode.	6	C402.3	L1,L2

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III A - SCHEME OF EVALUATION

Sem : VIII		Subject : fiber Optics & N/W	Sub Code : 15EC82	Date : 11/4/19		
Q. No.	Bit	Description		Marks	CO's	RBT LEVEL
1	a)	<p> P N I V_{BI} } 2M Photon $E = hf$ } 1M E_g CB VB } 3M </p> <p><u>Explanation under FB:</u> Majority carriers from P material (holes) cross over junction and combine with electrons of N material and vice-versa. Under favorable condⁿ, they combine radiatively to generate photons of energy $E = hf$. Each combination results in a photon.</p>		6	CO2.3	L1, L2
	b)	$I_r = 30 \text{ mA}$ $I_{nr} = 100 \text{ mA}$ $I = 40 \text{ mA}$ $\lambda = 1310 \text{ nm}$				
	a)	$I = \frac{I_r \cdot I_{nr}}{I_r + I_{nr}} = \frac{30 \times 100}{30 + 100} = 23.1 \text{ mA}$ (2M)		6	CO2.3	L1, L2
	b)	Int. quantum $\eta = \eta_{int} = \frac{I}{I_r} = \frac{23.1}{30} = 0.77$ (2M)				
	c)	$P_{int} = \eta_{int} \cdot \frac{I h c}{q \lambda} = \frac{4 \times 10^{-3} \times 6.625 \times 10^{-34} \times 3 \times 10^8}{1.602 \times 10^{-19} \times 1310 \times 10^{-9}}$ $P_{int} = 29.2 \text{ mW}$ (2M)				
2	a)	<p> E_2 E_1 E_2 E_1 E_2 E_1 $E = hf$ Photon $E = hf$ hf hf hf a) Photon absorption b) Spontaneous emission c) Stimulated emission </p>		6	CO2.3	L1, L2

M.H. Godege
Staff-In-Charge

Module Coordinator

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II IA - SCHEME OF EVALUATION

Sem : VIII		Subject : Fiber Optics & N/w	Sub Code : 15EC82	Date : 11/6/19		
Q. No.	Bit	Description	Marks	CO's	RBT LEVEL	
		<p>Explanation of 3 prours.</p> <p>- Condition of population inversion.</p> <p>b) <u>FB resonator laser:</u></p> <p>Reflective facets.</p> <p>confining layers.</p> <p>PN junction heterostructure.</p> <p>transverse size 0.1-1.2 um.</p> <p>longitudinal size 250-300 um.</p> <p>lateral size 5-15 um.</p> <p>Optical output</p> <p>30-50°</p> <p>5-10°</p>	06	2602.3	L1, L2	
		<p>Explanation of structure -</p> <p>- Method of providing feedback.</p> <p><u>DFB laser:-</u></p> <p>Corrugated Bragg grating</p> <p>confining layers</p> <p>Substrate</p> <p>active layer</p> <p>Optical output</p>				
		<p>Comparison in terms feedback mechanism</p>				

M. H. Dyaleq
Staff-In-Charge

Module Coordinator

HOD



II IA - SCHEME OF EVALUATION

Sem : VIII		Subject : Fiber Optics & NLW	Sub Code : ISEC82	Date : 11/4/19		
Q. No.	Bit	Description	Marks	CO's	RBT LEVEL	
Q3	a.	<p><u>Requirements of photo detectors:</u></p> <ol style="list-style-type: none"> 1) They should have high sensitivity & Responsivity at operating wavelength. 2) operating wavelength $\lambda_{(nm)} = 1.24/E_g(eV)$ should match to source wavelength. 3) Physical size should be compatible with fiber dimensions. 4) Should have longer lifespan, cheaper cost and easily available. L 2M. <p><u>PIN photo diode:</u></p> <p>2M.</p> <p><u>Explanation of construction & working</u> 3M.</p> <p>b) $L = 500 \mu m$ $R_1 = R_2 = 0.32$ $\alpha = 10/cm$</p> $g_{th} = \frac{\alpha + 1}{2L} \ln \left(\frac{1}{R_1 R_2} \right)$ <p>2M.</p> $= 10 + \frac{1}{2(500 \times 10^{-4})} \ln \left(\frac{1}{0.32^2} \right)$ <p>1M.</p> $g_{th} = 33 \text{ cm}^{-1}$ <p>3M.</p>	7	CO2,3	L1, L2	
			6M	CO2,2	L1, L2	

M.M. Godeg
Staff-In-Charge

Module Coordinator

HOD



II IA - SCHEME OF EVALUATION

Sem : VII		Subject : Fiber Optics & N/W	Sub Code : KTE 82	Date : 11/11/19		
Q. No.	Bit	Description	Marks	CO's	RBT LEVEL	
4	a.	<p>Photon → Photo Detector → Amplifier</p> <p># quanta shot noise $\langle I_p \rangle$</p> <p>Bias</p> <p>Amplifier Noise gain fluctuations.</p> <p>thermal noise $\langle i_t \rangle$</p> <p>Bulk dark current $\langle I_{DB} \rangle$</p> <p>Surface dark current $\langle I_{DS} \rangle$</p> <p>Surface leakage current $\langle I_{SL} \rangle$</p> <p>a) $\langle i_p \rangle^2 = 2q \cdot I_p \cdot B \cdot M^2 \cdot FCM$ $\langle i_{DB} \rangle^2 = 2q \cdot I_{DB} \cdot B \cdot M^2 \cdot FCM$ $\langle i_{DS} \rangle^2 = 2q \cdot I_{SL} \cdot B$ $\langle i_t \rangle^2 = \frac{4kTB}{R_L}$</p> <p>b) $I_p = \frac{hq\lambda}{hc} \cdot P_{in}$ $= \frac{0.65 \times 1.60 \times 10^{-19} \times 900 \times 10^9 \times 0.5 \times 10^{-6}}{6.625 \times 10^{-34} \times 3 \times 10^8}$ $I_p = 0.235 \mu A$ $M = \frac{I_M}{I_p} = \frac{10 \mu A}{0.235 \mu A} = 43$ \Rightarrow Primary current is multiplied by 43 times.</p>	7	CO2-3	L1, L2	
	b)	<p>$I_p = \frac{hq\lambda}{hc} \cdot P_{in}$ $= \frac{0.65 \times 1.60 \times 10^{-19} \times 900 \times 10^9 \times 0.5 \times 10^{-6}}{6.625 \times 10^{-34} \times 3 \times 10^8}$ $I_p = 0.235 \mu A$ $M = \frac{I_M}{I_p} = \frac{10 \mu A}{0.235 \mu A} = 43$ \Rightarrow Primary current is multiplied by 43 times.</p>	6	CO2-3	L1, L2	

M. N. Gedde
Staff-In-Charge

[Signature]
Module Coordinator

[Signature]
HOD